

FDS7764S

30V N-Channel PowerTrench® SyncFET™

General Description

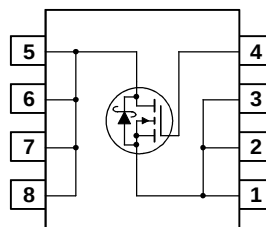
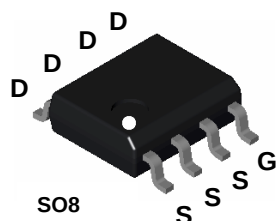
The FDS7764S is designed to replace a single SO-8 MOSFET and Schottky diode in synchronous DC:DC power supplies. This 30V MOSFET is designed to maximize power conversion efficiency, providing a low $R_{DS(ON)}$ and low gate charge. The FDS7764S includes an integrated Schottky diode using Fairchild's monolithic SyncFET technology.

Applications

- DC/DC converter
- Motor drives

Features

- 13.5 A, 30 V. $R_{DS(ON)} = 7.5\text{ m}\Omega @ V_{GS} = 10\text{ V}$
 $R_{DS(ON)} = 9.0\text{ m}\Omega @ V_{GS} = 4.5\text{ V}$
- Includes SyncFET Schottky body diode
- Low gate charge (25 nC typical)
- High performance trench technology for extremely low $R_{DS(ON)}$ and fast switching
- High power and current handling capability



Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-Source Voltage	30	V
V_{GSS}	Gate-Source Voltage	± 16	V
I_D	Drain Current – Continuous (Note 1a)	13.5	A
	– Pulsed	50	
P_D	Power Dissipation for Single Operation (Note 1a) (Note 1b) (Note 1c)	2.5	W
		1.2	
		1.0	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to $+150$	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	50	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	30	

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDS7764S	FDS7764S	13"	12mm	2500 units

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

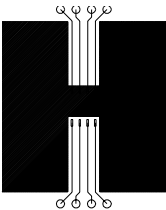
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 10\text{ mA}$, Referenced to 25°C		23		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$			500	μA
I_{GSSF}	Gate–Body Leakage, Forward	$V_{GS} = 16\text{ V}, V_{DS} = 0\text{ V}$			100	nA
I_{GSSR}	Gate–Body Leakage, Reverse	$V_{GS} = -16\text{ V}, V_{DS} = 0\text{ V}$			-100	nA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 1\text{ mA}$	0.8	1.4	2	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 10\text{ mA}$, Referenced to 25°C		-2		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = 10\text{ V}, I_D = 13.5\text{ A}$ $V_{GS} = 4.5\text{ V}, I_D = 12\text{ A}$ $V_{GS} = 10\text{ V}, I_D = 13.5\text{ A}, T_J = 125^\circ\text{C}$		6 7 8	7.5 9 10	m Ω
g_{FS}	Forward Transconductance	$V_{DS} = 10\text{ V}, I_D = 13.5\text{ A}$		72		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		2800		pF
C_{oss}	Output Capacitance			530		pF
C_{rss}	Reverse Transfer Capacitance			195		pF
R_G	Gate Resistance	$V_{GS} = 15\text{ mV}, f = 1.0\text{ MHz}$		1.4		Ω
Switching Characteristics (Note 2)						
$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = 15\text{ V}, I_D = 1\text{ A},$ $V_{GS} = 10\text{ V}, R_{GEN} = 6\text{ }\Omega$		9	18	ns
t_r	Turn–On Rise Time			7	14	ns
$t_{d(off)}$	Turn–Off Delay Time			46	74	ns
t_f	Turn–Off Fall Time			16	29	ns
Q_g	Total Gate Charge	$V_{DS} = 15\text{ V}, I_D = 13.5\text{ A},$ $V_{GS} = 5\text{ V}$		25	35	nC
Q_{gs}	Gate–Source Charge			6		nC
Q_{gd}	Gate–Drain Charge			6		nC

Electrical Characteristics

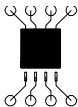
T_A = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Drain–Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain–Source Diode Forward Current				3.5	A
V _{SD}	Drain–Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 3.5 A (Note 2)		450	700	mV
t _{rr}	Diode Reverse Recovery Time	I _F = 3.5 A,		25		ns
Q _{rr}	Diode Reverse Recovery Charge	d _I /d _t = 300 A/μs (Note 2)		40		nC

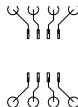
Notes:
1. R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{θJC} is guaranteed by design while R_{θCA} is determined by the user's board design.



a) 50°/W when mounted on a 1in² pad of 2 oz copper



b) 105°/W when mounted on a .04 in² pad of 2 oz copper



c) 125°/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300μs, Duty Cycle < 2.0%

Typical Characteristics

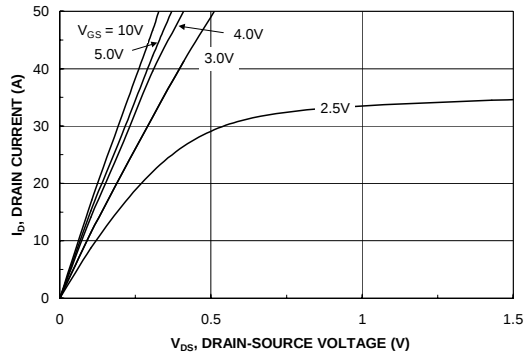


Figure 1. On-Region Characteristics.

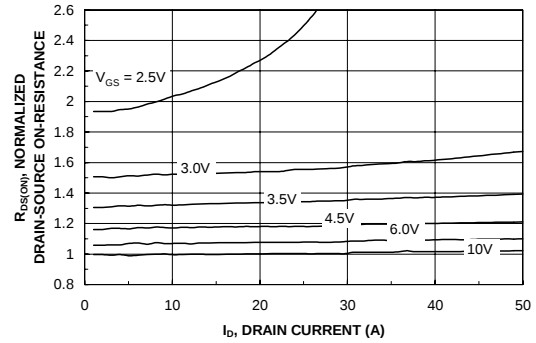


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

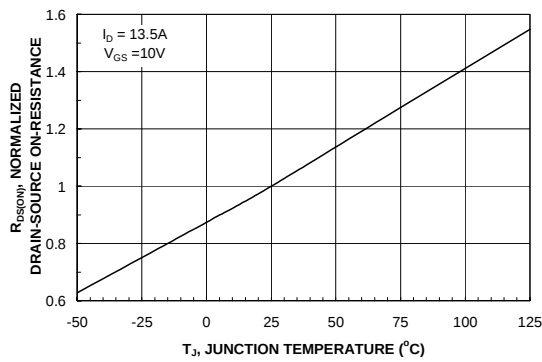


Figure 3. On-Resistance Variation with Temperature.

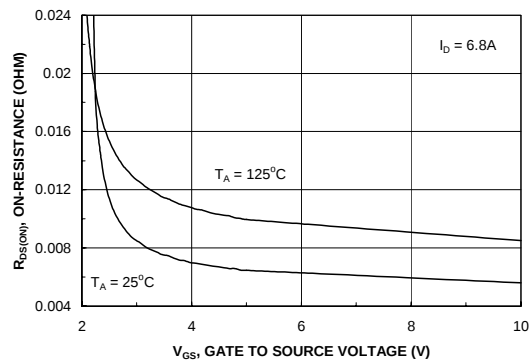


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

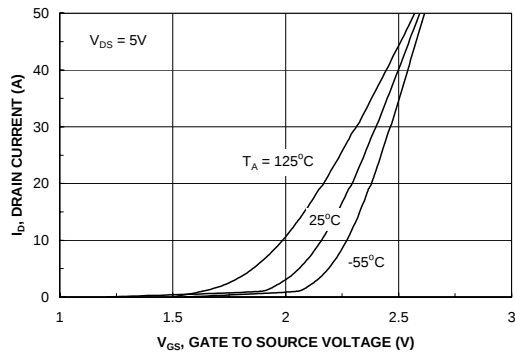


Figure 5. Transfer Characteristics.

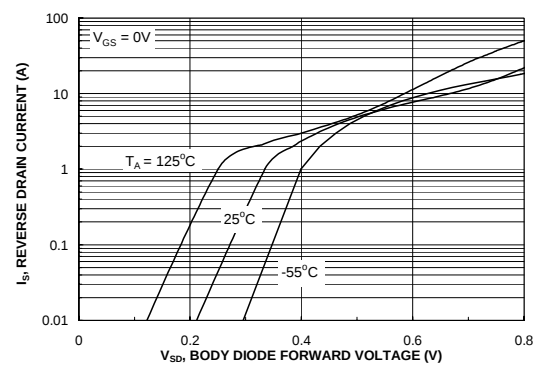


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

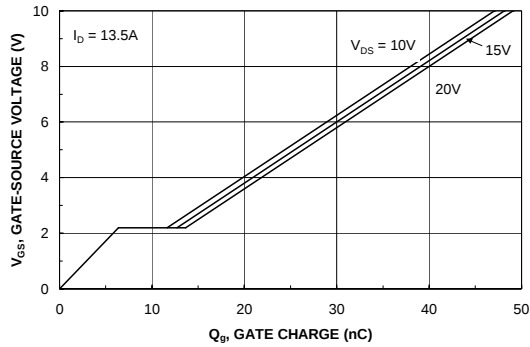


Figure 7. Gate Charge Characteristics.

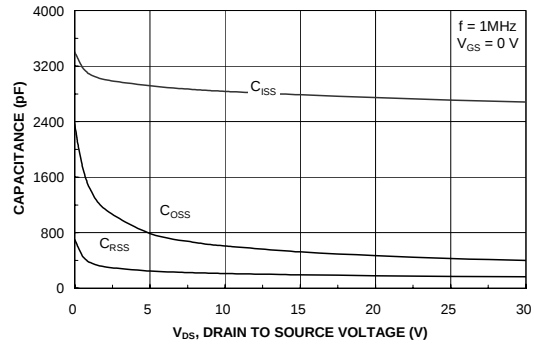


Figure 8. Capacitance Characteristics.

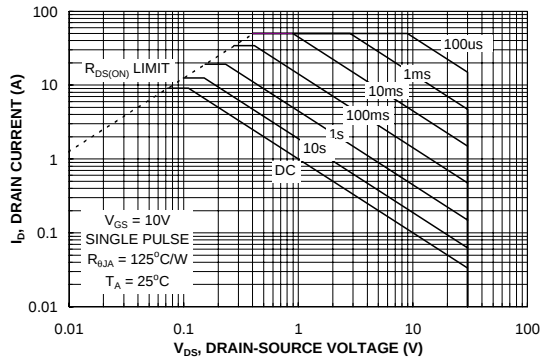


Figure 9. Maximum Safe Operating Area.

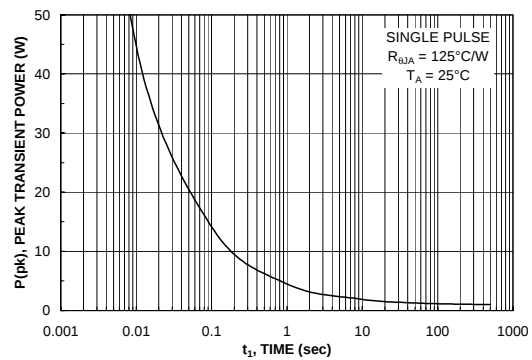


Figure 10. Single Pulse Maximum Power Dissipation.

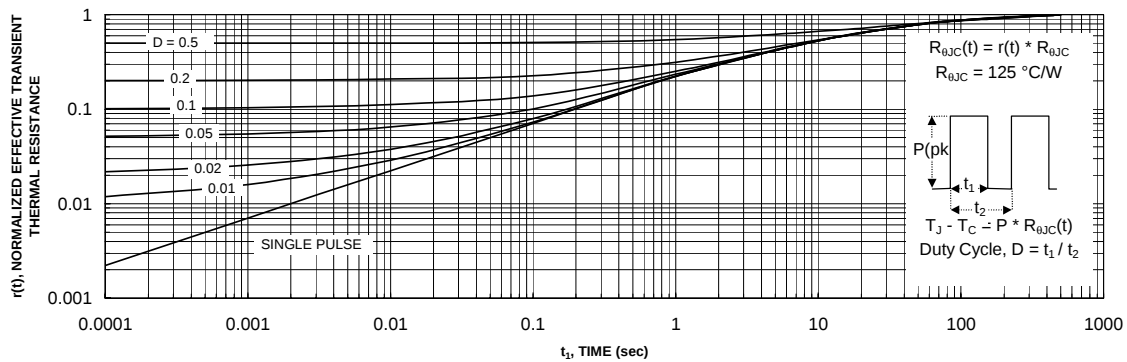


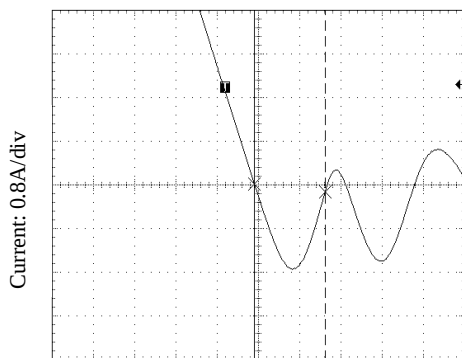
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.
Transient thermal response will change depending on the circuit board design.

Typical Characteristics (continued)

SyncFET Schottky Body Diode Characteristics

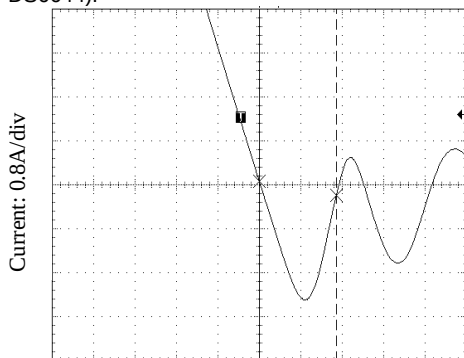
Fairchild's SyncFET process embeds a Schottky diode in parallel with PowerTrench MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 12 FDS7764S.



Time: 12.5ns/div

Figure 12. FDS7764S SyncFET body diode reverse recovery characteristic.

For comparison purposes, Figure 13 shows the reverse recovery characteristics of the body diode of an equivalent size MOSFET produced without SyncFET (FDS6644).



Time: 12.5ns/div

Figure 13. Non-SyncFET (FDS6644) body diode reverse recovery characteristic.

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

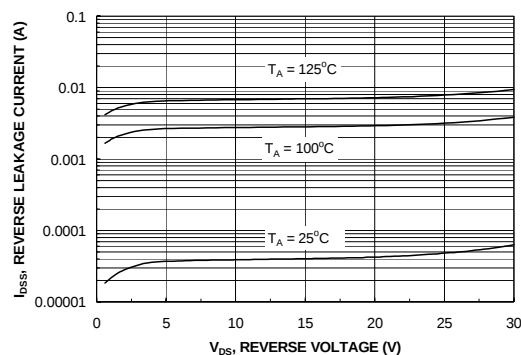


Figure 14. SyncFET diode reverse leakage versus drain-source voltage and temperature.

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACE ^{Ex} TM	FACT TM	ImpliedDisconnect TM	PACMAN TM	SPM TM
ActiveArray TM	FACT Quiet Series TM	ISOPLANAR TM	POP TM	Stealth TM
Bottomless TM	FAST [®]	LittleFET TM	Power247 TM	SuperSOT TM -3
CoolFET TM	FAST ^r TM	MicroFET TM	PowerTrench [®]	SuperSOT TM -6
CROSSVOLT TM	FRFET TM	MicroPak TM	QFET TM	SuperSOT TM -8
DOME TM	GlobalOptoisolator TM	MICROWIRE TM	QS TM	SyncFET TM
EcoSPARK TM	GTO TM	MSX TM	QT Optoelectronics TM	TinyLogic TM
E ² CMOS TM	HiSeC TM	MSXPro TM	Quiet Series TM	TruTranslation TM
EnSigna TM	I ² C TM	OCX TM	RapidConfigure TM	UHC TM
Across the board. Around the world. TM		OCXPro TM	RapidConnect TM	UltraFET [®]
The Power Franchise TM		OPTOLOGIC [®]	SILENT SWITCHER [®]	VCX TM
Programmable Active Droop TM		OPTOPLANAR TM	SMART START TM	

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.